

✓ Page 10, line 8, after "barrier" insert -layer-;

✓ Page 10, line 10, after "oxide" insert -film-; change "form" to -formed-; and change "reduces" to -reduce-;

✓ Page 10, line 12, after "structure" delete "is";

✓ Page 10, line 22, change "is focus" to -focuses-;

✓ Page 10, line 23. insert a hyphen between "above" and "described";

✓ Page 18, line 4, after "on" insert -the-.

IN THE CLAIMS:

Please amend claim 25 as follows:

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25. (amended) A pre-anneal intermediate structure in the formation of an isolation structure for a semiconductor device, comprising:
a semiconductor substrate having a first surface and a second surface;
at least one first doped area on said substrate first surface; and
a substantially dopant-free, uninterrupted diffusion barrier layer over said at least one first doped area on said substrate first surface.

26. (amended) The structure of claim 25 further comprising a layer of oxide between said substrate first surface and said substantially dopant-free, uninterrupted diffusion barrier layer.

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27. (amended) The structure of claim 25 wherein said substantially dopant-free, uninterrupted diffusion barrier layer extends over said substrate second surface.

28. (amended) The structure of claim 25 further comprising a second substantially dopant-free, uninterrupted diffusion barrier layer over said substrate second surface.